

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1863	NAND with source with drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/14 21:23
S2	1359	(NAND with source with drain) and semiconductor and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/15 06:35
S3	31	(NAND with source with drain) and semiconductor and slot and contact and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:47
S5	4	(NAND with source with drain) and semiconductor and (single adj mask\$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 09:52
S6	159	((memory adj cell) with source with drain) and semiconductor and (single adj mask\$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 13:24
S7	4	((("20020149081") or ("6115287") or ("6411548") or ("5780338")). PN.	US-PGPUB; USPAT	OR	OFF	2005/03/24 15:00
S8	0	((((memory adj cell) with source with drain) with (single adj mask \$6)) and semiconductor and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 13:24
S9	0	(NAND with source with drain with (single adj mask\$6)) and semiconductor and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/24 21:42

S10	0	(NAND with source with drain with (single adj mask\$6)) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/14 21:59
S11	2226	(438/586).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/05 13:02
S12	0	438/586.ccls. and (NAND with source with drain) and semiconductor and (single adj mask\$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/27 12:37
S13	1	"438"/\$.ccls. and (NAND with source with drain) and semiconductor and (single adj mask\$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 10:20
S14	4	"257"/\$.ccls. and (NAND with source with drain) and semiconductor and (single adj mask\$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 10:24
S15	0	("257"/\$.ccls. with source with drain) and semiconductor and (single adj mask\$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 10:25
S16	0	("438"/\$.ccls. with source with drain) and semiconductor and (single adj mask\$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/14 08:11
S17	0	((("438"/\$.ccls.) with source with drain) and semiconductor and (single adj mask\$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 10:25
S18	0	((("257"/\$.ccls.) with source with drain) and semiconductor and (single adj mask\$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 10:26

S19	0	((("257"/\$.ccls.) with source with drain) and (single adj mask\$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 10:26
S20	0	((("438"/\$.ccls.) with source with drain) and (single adj mask\$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/19 06:45
S21	0	((("438"/\$.ccls.) with source with drain) and (single adj mask\$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/19 06:45
S22	6	((NAND) with source with drain) and (single adj mask\$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/19 06:55
S23	6	((("20020149081") or ("6115287") or ("6411548")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/19 06:55
S24	2218	("NAND") with source with drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/27 12:25
S25	40	("NAND") with source with drain with mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/27 12:28
S26	3	("NAND") with source with drain with (single adj mask)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/27 12:25
S27	36	((("NAND") with source with drain with mask) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/27 12:28

S28	1	438/586.ccls. and (NAND with source with drain) and semiconductor and (single adj mask\$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/27 12:38
S29	2	("NAND") and (source adj slot) and (drain adj contact) and (source adj select adj (gate or electrode)) and (drain adj select adj (gate or electrode)) and ((single or one) adj mask\$4) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 10:01
S30	2	((memory adj array) or ("NAND") adj flash adj memory) or ((field adj effect adj transistor or ("FET")) and (source adj slot) and (drain adj contact) and (source adj select adj (gate or electrode)) and (drain adj select adj (gate or electrode)) and ((single or one) adj mask\$4) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 10:04
S31	271	((memory adj array) or ("NAND") adj flash adj memory) or ((field adj effect adj transistor or ("FET")) and (source) and (drain) and (source adj (gate or electrode or contact)) and (drain adj (gate or electrode or contact)) and ((single or one) adj mask\$4) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 10:05
S32	144	((memory adj array) or ("NAND") adj flash adj memory) or ((field adj effect adj transistor or ("FET")) and (source) and (drain) and (source adj (gate or electrode or contact)) and (drain adj (gate or electrode or contact)) and ((single) adj mask\$4) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 10:22
S33	144	((memory adj array) or ("NAND") adj flash adj memory) or ((field adj effect adj transistor or ("FET")) and (source adj (gate or electrode or contact)) and (drain adj (gate or electrode or contact)) and ((single) adj mask \$4) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 10:06

S34	0	(((((memory adj array) or ("NAND") adj flash adj memory)) or ((field adj effect adj transistor) or ("FET")))) and (source) and (drain) and (source adj (gate or electrode or contact)) and (drain adj (gate or electrode or contact))) with ((single or one) adj mask\$4)) and ((single) adj mask\$4) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 10:23
S35	0	(((((memory adj array) or ("NAND") adj flash adj memory)) or ((field adj effect adj transistor) or ("FET")))) and (source) and (drain) and (source adj (gate or electrode or contact)) and (drain adj (gate or electrode or contact))) near ((single or one) adj mask\$4)) and ((single) adj mask\$4) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 10:23
S36	2	(((((memory adj array) or ("NAND") adj flash adj memory)) or ((field adj effect adj transistor) or ("FET")))) and (source) and (drain) and (source adj (gate or electrode or contact)) and (drain adj (gate or electrode or contact))) same ((single or one) adj mask\$4)) and ((single) adj mask\$4) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 10:24
S37	144	(((((memory adj array) or ("NAND") adj flash adj memory)) or ((field adj effect adj transistor) or ("FET")))) and (source) and (drain) and (source adj (gate or electrode or contact)) and (drain adj (gate or electrode or contact))) and ((single or one) adj mask\$4)) and ((single) adj mask\$4) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 10:25
S38	2	10/692430	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 13:16
S39	5	("20020048829" "6277679" "6469317" "6706544" "6872604").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/01/05 09:45
S40	184	(NAND) and semiconductor and (single adj mask\$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 10:00

S41	2	(NAND) and semiconductor and (single adj mask\$6) and @ad<="20031023" and (source adj select) and (drain adj select)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/08 08:53
S42	5	("4435790" "4637128" "5262985" "5416738" "5514889").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/01/05 11:01
S43	45	("5687118").URPN.	USPAT	OR	ON	2007/01/05 11:00
S44	4	((("6448606") or ("6878588")).PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/05 10:18
S45	2	semiconductor and (single adj mask\$6) and @ad<="20031023" and (((flash adj memory) or (non-volatile adj memory) or ((electrically-erasable adj programmable adj read-only adj memory) or ("EEPROM")) or ("NAND")) adj (array or string)) and (source adj select) and (drain adj select)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 11:01
S46	2	semiconductor and (single adj mask\$6) and @ad<="20031023" and ((flash adj memory) or (non-volatile adj memory) or ((electrically-erasable adj programmable adj read-only adj memory) or ("EEPROM")) or ("NAND")) and (source adj select) and (drain adj select)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 10:46
S47	5	("4435790" "4637128" "5262985" "5416738" "5514889").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/01/05 10:59
S48	45	("5687118").URPN.	USPAT	OR	ON	2007/01/05 11:00
S49	0	((("5687118").URPN.) and (single adj mask\$4)	USPAT	OR	ON	2007/01/05 11:00
S50	0	((("4435790" "4637128" "5262985" "5416738" "5514889").PN.) and (single adj mask\$4)	US-PGPUB; USPAT; USOCR	OR	ON	2007/01/05 11:01

S51	0	(semiconductor and (single adj mask\$6) and @ad<="20031023" and (((flash adj memory) or (non-volatile adj memory) or ((electrically-erasable adj programmable adj read-only adj memory) or ("EEPROM")) or ("NAND")) adj (array or string)) and (source adj select) and (drain adj select)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 11:01
S52	0	(semiconductor and (single adj mask\$6) and (((flash adj memory) or (non-volatile adj memory) or ((electrically-erasable adj programmable adj read-only adj memory) or ("EEPROM")) or ("NAND")) adj (array or string)) and (source adj select) and (drain adj select)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 11:02
S53	0	(semiconductor and (single adj mask\$6) and (((flash adj memory) or (non-volatile adj memory) or ((electrically-erasable adj programmable adj read-only adj memory) or ("EEPROM")) or ("NAND")) adj (array or string)) and (source adj select) and (drain adj select)).clm.	US-PGPUB	OR	ON	2007/01/05 11:02
S54	5	(semiconductor and (single adj mask\$6) and (((flash adj memory) or (non-volatile adj memory) or ((electrically-erasable adj programmable adj read-only adj memory) or ("EEPROM")) or ("NAND")) adj (array or string)) and (source adj select) and (drain adj select))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/08 09:04
S55	8	("20010000306" "6201732" "6310800" "6404681" "6438030" "6451652" "6606265" "6649453").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/01/05 11:05
S56	0	("7075140").URPN.	USPAT	OR	ON	2007/01/05 11:06
S57	8	("20010000306" "6201732" "6310800" "6404681" "6438030" "6451652" "6606265" "6649453").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/01/05 12:30

S58	3	"365"/\$.ccls. and (semiconductor and (single adj (mask\$6 or photo or photoresist or resist)) and (((flash adj memory) or (non-volatile adj memory) or ((electrically-erasable adj programmable adj read-only adj memory) or ("EEPROM")) or ("NAND")) adj (array or string)) and (source adj select) and (drain adj select))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 12:40
S59	54	"365"/\$.ccls. and (semiconductor and (single adj (mask\$6 or photo or photoresist or resist)) and (((flash adj memory) or (non-volatile adj memory) or ((electrically-erasable adj programmable adj read-only adj memory) or ("EEPROM")) or ("NAND")) adj (array or string)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 12:41
S60	9	("4099196" "4314265" "4409723" "4503519" "4531203" "4561004" "4639893" "4763299" "4905995").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/01/05 12:59
S61	521	(438/201).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/05 13:03
S62	567	(438/266).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/05 13:37
S63	180	(438/260).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/05 13:04
S64	349	(438/211).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/05 13:15
S65	2	10/907959	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 13:25

S66	2828	(438/257).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/05 13:37
S67	2	semiconductor and @ad<="20031023" and (source adj select) and (drain adj select) and (single adj mask\$6)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/14 22:23
S68	2	((("7075140") or ("5687118"))).PN.	USPAT	OR	OFF	2007/01/08 08:58
S69	0	(semiconductor and (single adj mask\$6) and (((flash adj memory) or (non-volatile adj memory) or ((electrically-erasable adj programmable adj read-only adj memory) or ("EEPROM")) or ("NAND")) adj (array or string)) and (source adj contact) and (drain adj contact))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/08 09:05
S70	3	(semiconductor and (single adj mask\$6) and (((flash adj memory) or (non-volatile adj memory) or ((electrically-erasable adj programmable adj read-only adj memory) or ("EEPROM")) or ("NAND")) adj (array or string)) and (source adj (contact or electrode)) and (drain adj (contact or electrode)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/08 09:05
S71	2	10/692430	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/14 22:37
S72	2	10/911516	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/14 08:16
S73	14	("20010023120" "20010032995" "20020064970" "3796182" "5000113" "5364664" "6040022" "6159854" "6444137" "6451686" "6482752" "6486080" "6642131" "6962824").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/14 15:39
S77	2	((("4977098") or ("4904620"))).PN.	USPAT	OR	OFF	2007/06/25 11:53

S78	9	("4904620").URPN.	USPAT	OR	ON	2007/06/14 16:25
S79	19	("3640811" "4042953" "4106051" "4128670" "4265935" "4301588" "4309812" "4337476" "4359490" "4488166" "4504521" "4557943" "4568565" "4579609" "4605479" "4668530" "4679310" "4777150" "4904620").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/14 16:33
S80	0	((("NAND") adj (flash adj memory)) adj (string or series)) and @ad<="20031023" and (single adj mask\$6)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/14 22:26
S81	9	((("NAND") adj (flash adj memory))) and @ad<="20031023" and (single adj mask\$6)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/14 22:26
S82	9	((("NAND") adj (flash adj memory)) and @ad<="20031023" and (single adj mask\$6)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/14 22:33
S83	16	(lindsay.in.) and roger and ("NAND")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/14 22:38
S84	0	semiconductor and (flahs adj memory) and (source adj (contact or electrode)) and (drain adj (contact or electrode)) and @ad<="20031023" and ("NAND")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/15 06:37
S85	218	semiconductor and (flash adj memory) and (source adj (contact or electrode)) and (drain adj (contact or electrode)) and @ad<="20031023" and ("NAND")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/15 06:37
S86	3	S85 and (single adj (mask\$4 or photoresist or resist))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/15 06:39

S87	105	S85 and (mask\$4 or photoresist or resist)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/15 07:01
S89	2	((("6121664") or ("5,687,118")). PN.	USPAT	OR	OFF	2007/06/25 11:55
S90	18	("NAND") and (source adj select adj gate) and (drain adj select adj gate) and (floating adj (gate or electrode)) and contact and memory and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/24 21:54
S91	1	11/209301	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/24 21:46
S92	19	((("NAND") or ("NOR")) and (source adj select adj gate) and (drain adj select adj gate) and (floating adj (gate or electrode)) and contact and memory and @ad<="20031023")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/24 21:55
S93	2	((("NAND") and source and drain) same (single adj mask\$6)) and semiconductor and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 21:20
S94	0	((("NAND") and source and drain) same (single adj mask\$6)) and semiconductor).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 21:20
S95	0	((("NAND") and source and drain) same (single adj mask\$6)) and semiconductor).clm.	US-PGPUB	OR	ON	2008/04/24 21:20
S96	123	((("NAND") and source and drain) and (single adj mask\$6)) and semiconductor and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 21:21
S97	0	((("NAND") and source and drain) and (single adj mask\$6)) and semiconductor).clm.	US-PGPUB	OR	ON	2008/04/24 21:21

S98	3389	(438/257).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/24 21:24
S99	2637	257/e21.507.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 21:27
S100	539	257/e21.235.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 21:27
S101	231	257/e21.691.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 21:27
S102	1458	257/e21.679.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 21:27
S103	105	257/e21.015.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 21:27
S104	686	(438/266).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/24 21:28

4/ 28/ 08 9:01:59 AM

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